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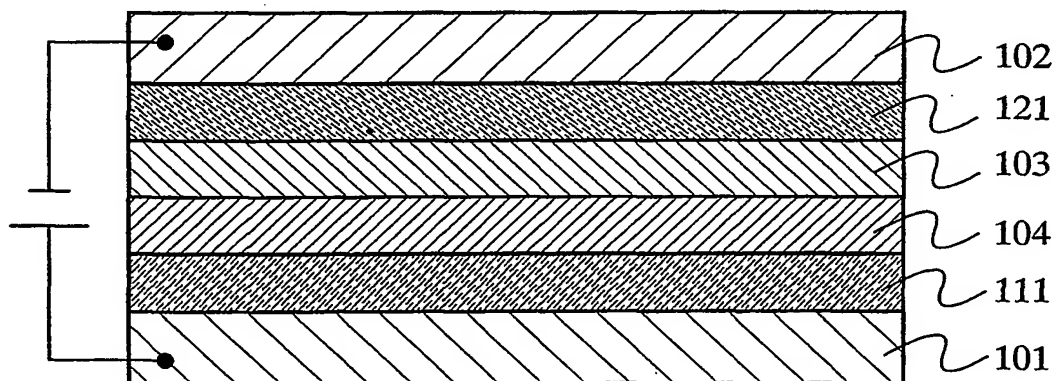
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ning of each regular issue of the PCT Gazette.

(54) Title: LIGHT EMITTING ELEMENT AND LIGHT EMITTING DEVICE



(57) Abstract: A light emitting element of the invention includes n pieces of light emitting layers (n is a natural number) between first and second electrodes. A first layer and a second layer are provided between the mth light emitting layer (m is a natural number of $1 \leq m \leq n$) and the m + 1th light emitting layer. The first and second layers are contacted to each other. The first layer contains a substance that transports holes easily and a substance with an electron accepting property. The second layer contains a substance that transports electrons easily and a substance with an electron donating property. Molybdenum oxide is used as the substance with the electron accepting property.